

Silizium-PIN-Fotodiode mit sehr kurzer Schaltzeit Silicon PIN Photodiode with Very Short Switching Time

SFH 229
SFH 229 FA



SFH 229



SFH 229 FA

Wesentliche Merkmale

- Speziell geeignet für Anwendungen im Bereich von 380 nm bis 1100 nm (SFH 229) und bei 880 nm (SFH 229 FA)
- Kurze Schaltzeit (typ. 10 ns)
- 3 mm-Plastikbauform im LED-Gehäuse
- Auch gegurtet lieferbar

Anwendungen

- Lichtschranken für Gleich- und Wechselbetrieb
- Industrieelektronik
- „Messen/Steuern/Regeln“

Features

- Especially suitable for applications from 380 nm to 1100 nm (SFH 229) and of 880 nm (SFH 229 FA)
- Short switching time (typ. 10 ns)
- 3 mm LED plastic package
- Also available on tape and reel

Applications

- Photointerrupters
- Industrial electronics
- For control and drive circuits

Typ Type	Bestellnummer Ordering Code
SFH 229	Q62702-P215
SFH 229 FA	Q62702-P216

Grenzwerte
Maximum Ratings

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Betriebs- und Lagertemperatur Operating and storage temperature range	$T_{op}; T_{stg}$	- 40 ... + 100	°C
Löttemperatur (Lötstelle 2 mm vom Gehäuse entfernt bei Lötzeit $t \leq 3$ s) Soldering temperature in 2 mm distance from case bottom ($t \leq 3$ s)	T_S	230	°C
Sperrspannung Reverse voltage	V_R	20	V
Verlustleistung Total power dissipation	P_{tot}	150	mW

Kennwerte ($T_A = 25$ °C)
Characteristics

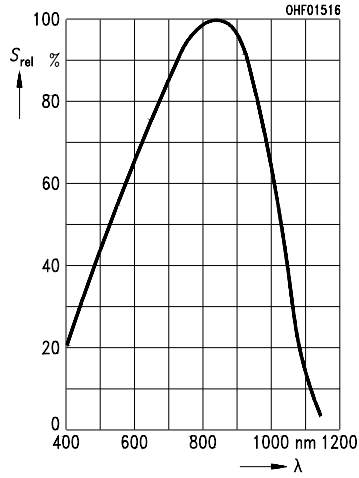
Bezeichnung Parameter	Symbol Symbol	Wert Value		Einheit Unit
		SFH 229	SFH 229 FA	
Fotostrom Photocurrent $V_R = 5$ V, Normlicht/standard light A, $T = 2856$ K, $E_V = 1000$ lx $V_R = 5$ V, $\lambda = 950$ nm, $E_e = 1$ mW/cm ²	I_P	28 (≥ 18)	–	μ A
	I_P	–	20 (≥ 10.8)	μ A
Wellenlänge der max. Fotoempfindlichkeit Wavelength of max. sensitivity	$\lambda_{S\ max}$	860	900	nm
Spektraler Bereich der Fotoempfindlichkeit $S = 10\%$ von S_{max} Spectral range of sensitivity $S = 10\%$ of S_{max}	λ	380 ... 1100	730 ... 1100	nm
Bestrahlungsempfindliche Fläche Radiant sensitive area	A	0.3	0.3	mm ²
Abmessung der bestrahlungsempfindlichen Fläche Dimensions of radiant sensitive area	$L \times B$ $L \times W$	0.56 × 0.56	0.56 × 0.56	mm × mm
Abstand Chipoberfläche zu Gehäuseoberfläche Distance chip front to case surface	H	2.4 ... 2.8	2.4 ... 2.8	mm
Halbwinkel Half angle	φ	± 17	± 17	Grad deg.

Kennwerte ($T_A = 25\text{ °C}$)

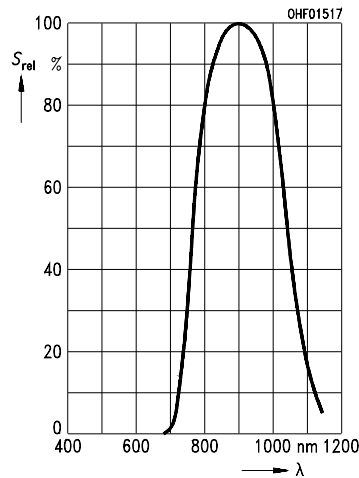
Characteristics (cont'd)

Bezeichnung Parameter	Symbol Symbol	Wert Value		Einheit Unit
		SFH 229	SFH 229 FA	
Dunkelstrom, $V_R = 10\text{ V}$ Dark current	I_R	50 (≤ 5000)	50 (≤ 5000)	μA
Spektrale Fotoempfindlichkeit, $\lambda = 850\text{ nm}$ Spectral sensitivity	S_λ	0.62	0.60	A/W
Quantenausbeute, $\lambda = 850\text{ nm}$ Quantum yield	η	0.90	0.88	<u>Electrons</u> Photon
Leerlaufspannung Open-circuit voltage $E_V = 1000\text{ lx}$, Normlicht/standard light A, $T = 2856\text{ K}$ $E_e = 0.5\text{ mW/cm}^2$, $\lambda = 950\text{ nm}$	V_O	450 (≥ 400)	–	mV
	V_O	–	420 (≥ 370)	mV
Kurzschlußstrom Short-circuit current $E_V = 1000\text{ lx}$, Normlicht/standard light A, $T = 2856\text{ K}$ $E_e = 0.5\text{ mW/cm}^2$, $\lambda = 950\text{ nm}$	I_{SC}	27	–	μA
	I_{SC}	–	9	μA
Anstiegs- und Abfallzeit des Fotostromes Rise and fall time of the photocurrent $R_L = 50\ \Omega$; $V_R = 10\text{ V}$; $\lambda = 850\text{ nm}$; $I_p = 800\ \mu\text{A}$	t_r, t_f	10	10	ns
Durchlaßspannung, $I_F = 100\text{ mA}$, $E = 0$ Forward voltage	V_F	1.3	1.3	V
Kapazität, $V_R = 0\text{ V}$, $f = 1\text{ MHz}$, $E = 0$ Capacitance	C_0	13	13	pF
Temperaturkoeffizient von V_O Temperature coefficient of V_O	TC_V	– 2.6	– 2.6	mV/K
Temperaturkoeffizient von I_{SC} Temperature coefficient of I_{SC} Normlicht/standard light A $\lambda = 950\text{ nm}$	TC_I	0.18 –	– 0.2	%/K
Rauschäquivalente Strahlungsleistung Noise equivalent power $V_R = 10\text{ V}$, $\lambda = 850\text{ nm}$	NEP	6.5×10^{-15}	6.5×10^{-15}	$\frac{\text{W}}{\sqrt{\text{Hz}}}$
Nachweisgrenze, $V_R = 10\text{ V}$, $\lambda = 850\text{ nm}$ Detection limit	D^*	8.4×10^{12}	8.4×10^{12}	$\frac{\text{cm} \times \sqrt{\text{Hz}}}{\text{W}}$

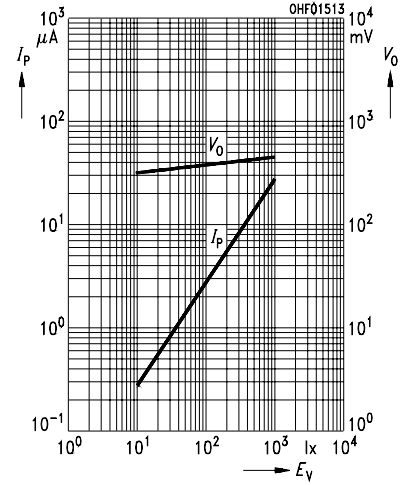
Relative Spectral Sensitivity
 $S_{rel} = f(\lambda)$
SFH 229



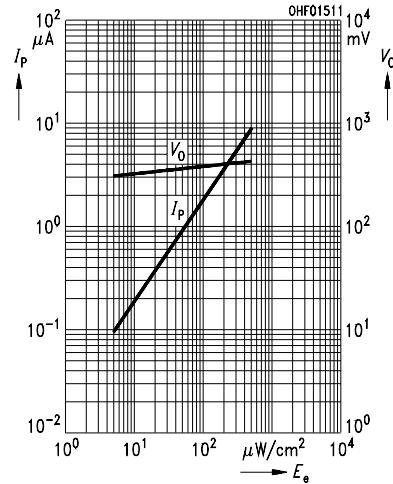
Relative Spectral Sensitivity
 $S_{rel} = f(\lambda)$
SFH 229 FA



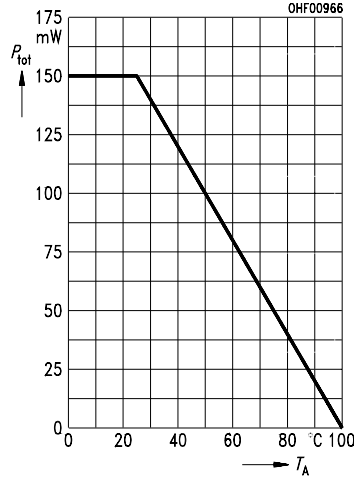
Photocurrent $I_P = f(E_v)$, $V_R = 5 V$
Open-Circuit Voltage $V_O = f(E_v)$
SFH 229



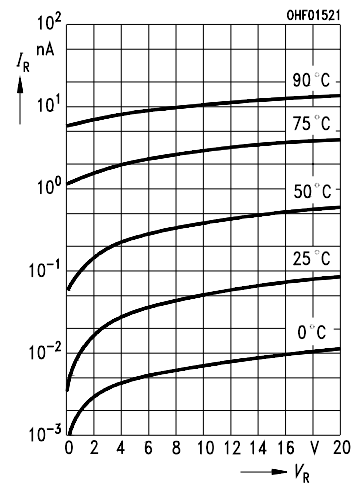
Photocurrent $I_P = f(E_e)$, $V_R = 5 V$
Open-Circuit Voltage $V_O = f(E_e)$
SFH 229 FA



Total Power Dissipation
 $P_{tot} = f(T_A)$

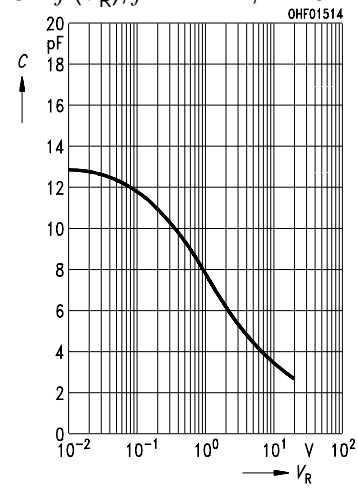


Dark Current
 $I_R = f(V_R), E = 0$



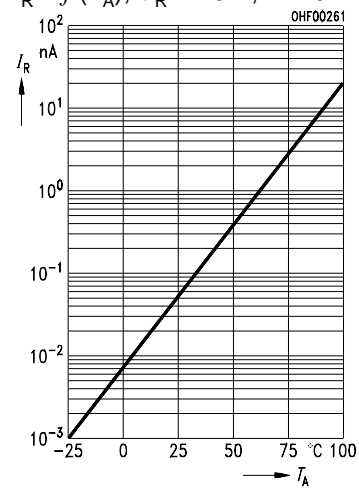
Capacitance

$C = f(V_R), f = 1 \text{ MHz}, E = 0$



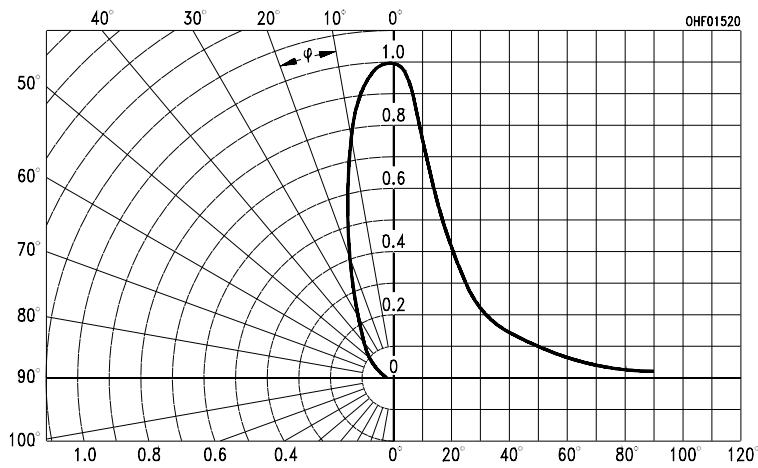
Dark Current

$I_R = f(T_A), V_R = 10 \text{ V}, E = 0$

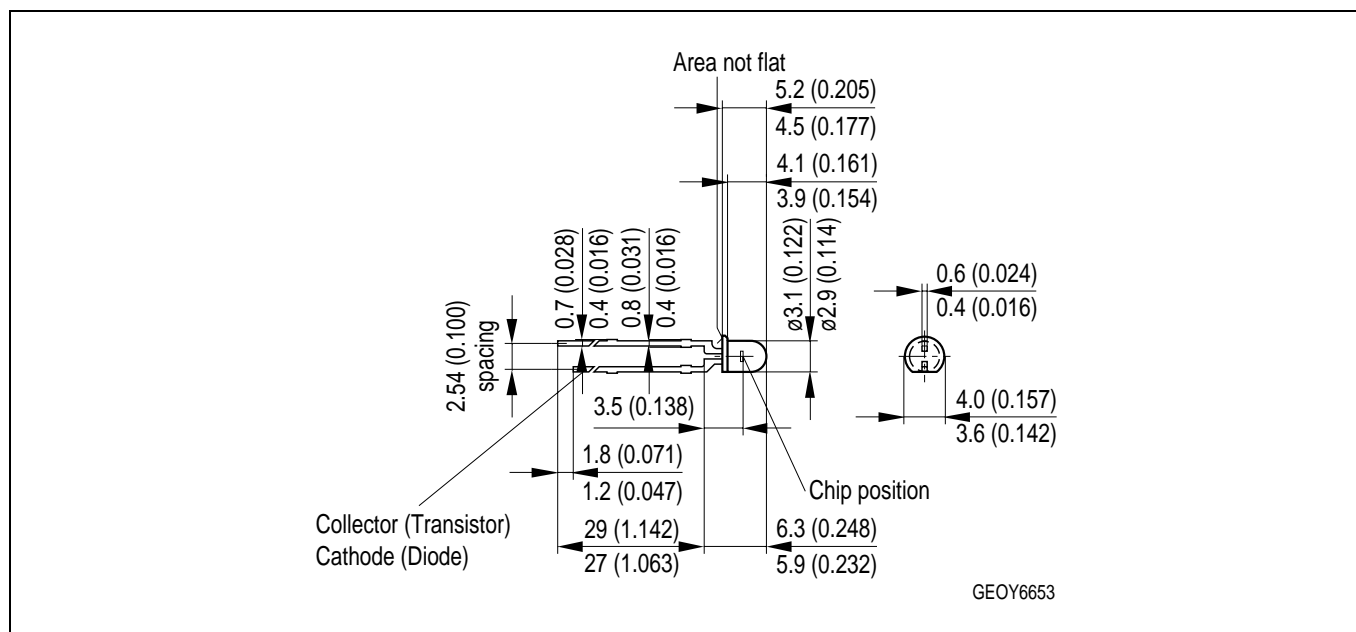


Directional Characteristics

$S_{\text{rel}} = f(\varphi)$



Maßzeichnung Package Outlines



Maße werden wie folgt angegeben: mm (inch) / Dimensions are specified as follows: mm (inch).

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